

NSH045N100S

N-Channel Enhanced Shielded Gate Trench Power MOSFET



Voltage: 100 Volts

Current: 120.0 Amperes

Polarity And Marking

Package: TO-252

Features

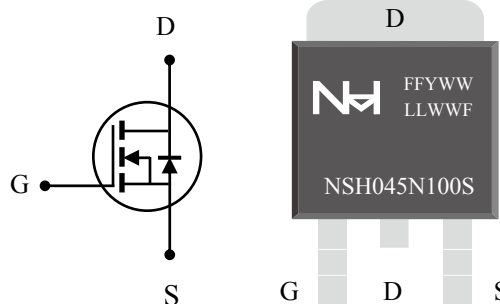
- NH'S Advanced SGT Technology
- Low Reverse Transfer Capacitances
- Low Gate Charge For Low Switching Loss
- Excellent $Q_g \cdot R_{ds(on)}$ Product(FOM)

Typical Applications

- Synchronous Rectification
- High-Frequency Circuits
- The Motor Drives
- Automotive Electronics
- Weight: App. 0.321 Grams (0.011323 Ounce)

Product Summary

V _{DS} Min.@T _j	100	V
I _D Min.@T _a	120.0	A
R _{DS(ON)} Typ.@10V	5	mΩ



Remark:

- ①. NH=Niuhang Trademark
- ②. FF=Product Line Code, According To Actual Changes
YWW=Date Code, According To Actual Changes
LLWWF=Internal Code, According To Actual Changes
- ③. NSH045N100S=Model

***100% UIS TESTED**

***100% ΔV_{DS} TESTED**

Absolute Maximum Ratings (T_a=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	T _a = 25 ℃	I _D	120.0	A
	T _a = 100 ℃		76.8	
Drain Current-Pulse (Note 1)	T _j < 150 ℃	I _{DM}	480	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25℃	T _a = 25 ℃	P _D	179	W
	T _a = 100 ℃		71	
Derating Factor		D _F	1.43	W/℃
Avalanche Current, Single Pulse (Note 1)	L= 0.5 mH	I _{AS}	32.0	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.16	L= 0.5 mH I _{AS} = 32.0 A, R _G = 10.0 Ω Starting T _j =25 ℃, V _G = 10.0 V	E _{AS}	256	mJ

Thermal Characteristics (T_a=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 150	℃
Storage Temperature Range		T _{STD}	-55 to 150	℃
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With T _a =25℃	R _{θJA}	100.0	℃/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	R _{θJC}	0.70	

Notes: 1. Pulse Width Limited By Max. Junction Temperature. (See Fig. 13).

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	BV _{DSS}	100	--	--	V
Bvdss Temperature Coefficient	ID=250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.11	--	V/℃
Drain-Source Leakage Current	VDS= 100 V,VGS=0V	I _{DSS}	--	--	1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= 20.0 A,VDS= 5 V	g _{fs}	--	40.0	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=250uA	V _{GS(TH)}	2.0	3.0	4.0	V
Drain-Source On Resistance	ID= 20.0 A,VGS= 10.0 V	R _{DS(ON)}	--	4.5	5.0	mΩ
	ID= 20.0 A,VGS= 4.5 V		--	5.2	6.7	
Dynamic Characteristics						
Gate Resistance	VGS=0V,VDS=0V, Freq.=1MHz	R _g	--	2.30	--	Ω
Input Capacitance	VDS= 50 V	C _{iss}	--	4500.0	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	970.0	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	30.0	--	pF
Switching Paramters (Test Circuit & Waveform See Fig.14)						
Turn-On Delay Time	VDS= 50 V	t _{d(on)}	--	28.0	--	ns
Turn-On Rise Time	VGS= 10.0 V	t _r	--	32.0	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	48.0	--	ns
Turn-Off Rise Time		t _f	--	27.0	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.15)						
Total Gate Charge	VDS= 50 V	Q _g	--	90.0	--	nC
Gate-Source Charge	VGS= 10.0 V	Q _{gs}	--	28.0	--	nC
Gate-Drain Charge	ID= 20.0 A	Q _{gd}	--	19.0	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.17)						
Max. Diode Forward Cuurent		I _S	--	--	120.0	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	420.0	A
Diode Forward Voltage	ID= 20.0 A,VGS=0V	V _{SD}	--	0.80	1.1	V
Reverse Recovery Time	ID= 20.0 A,di/dt= 100 A/us	t _{rr}	--	80.0	--	ns
Reverse Recovery Charge	VGS= 10.0 V,VDD= 50 V	Q _{rr}	--	190.0	--	nC

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Typical Characteristics Curves

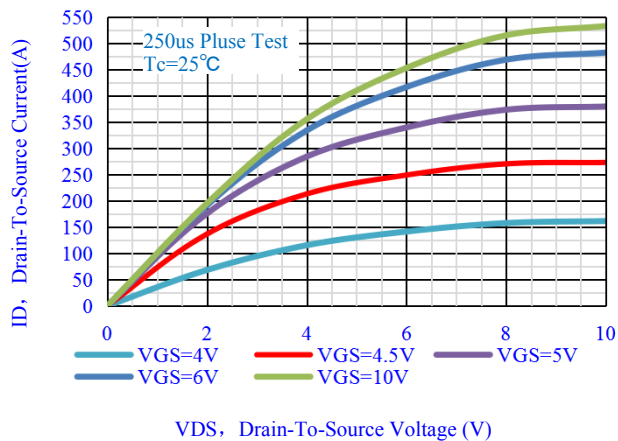


Fig.1-Output Characteristics

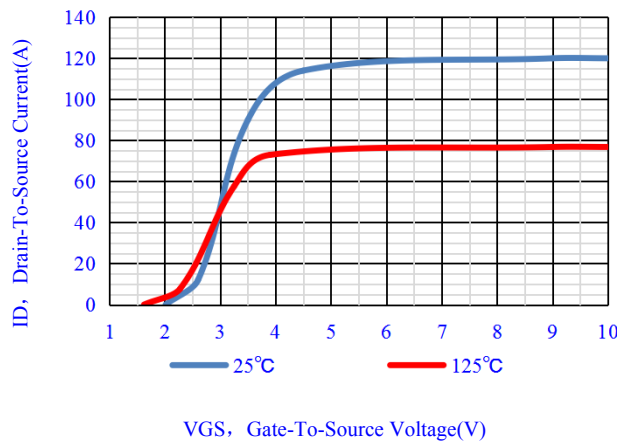


Fig.2- Transfer Characteristics

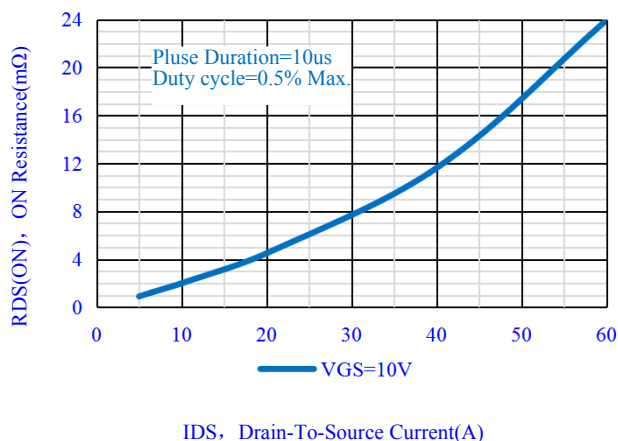


Fig.3- On Resistance vs. Drain Current

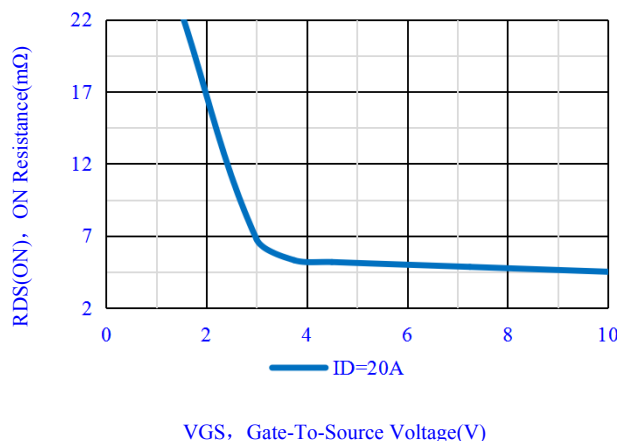


Fig.4- On Resistance vs. Gate Source Voltage

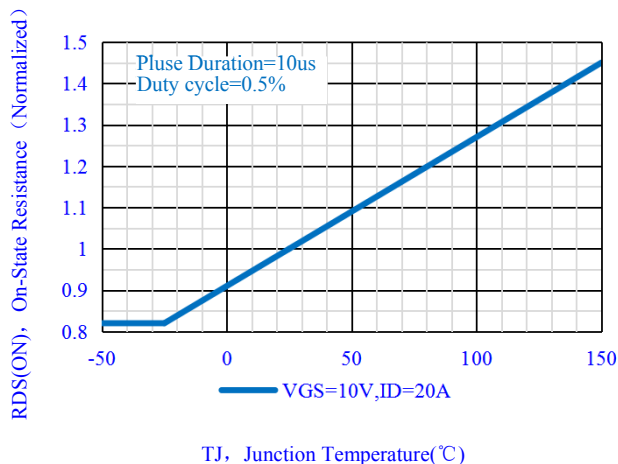


Fig.5- On Resistance vs. Junction Temperature

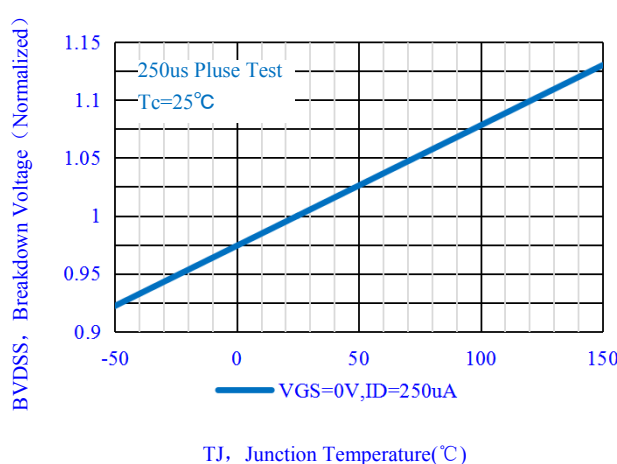


Fig.6- Breakdown Voltage vs. Junction Temperature

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Typical Characteristics Curves

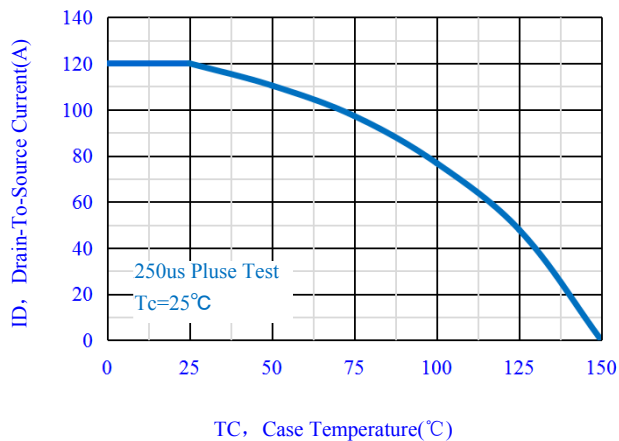


Fig.7-Maximum Continuous Drain Current vs. Case Temperature

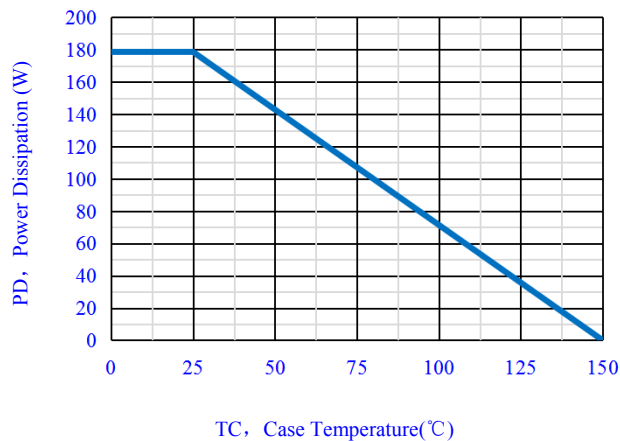


Fig.8-Maximum Power Dissipation vs. Case Temperature

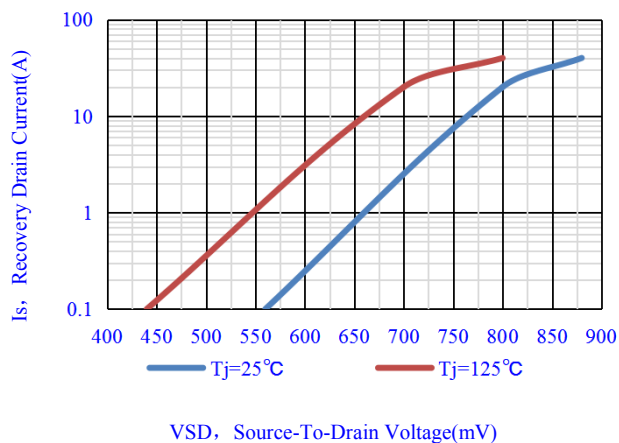


Fig.9- Source-To-Drain Diode Forward Voltage

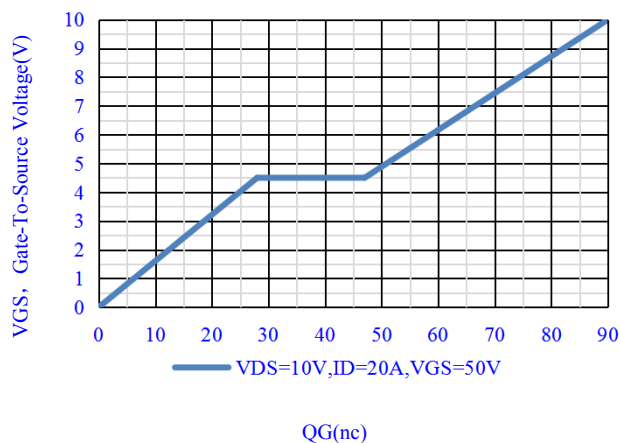


Fig.10-Gate Charge Waveform

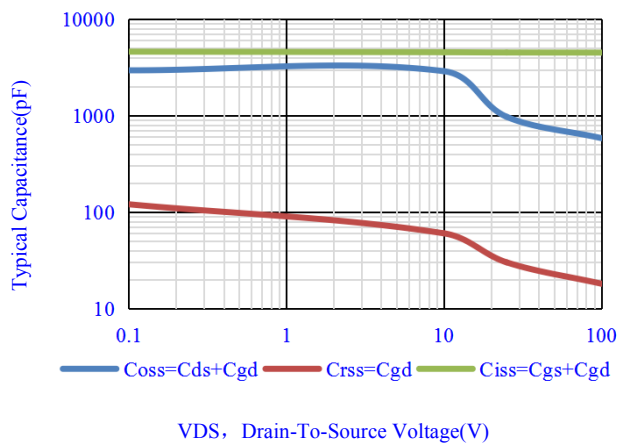


Fig.11-Typical Capacitance vs. Drain-To-Source Voltage

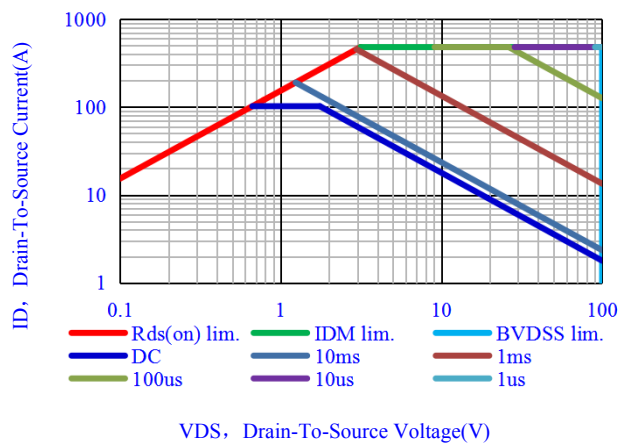


Fig.12-Maximum Safe Operating Area(SOA)

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Typical Characteristics Curves

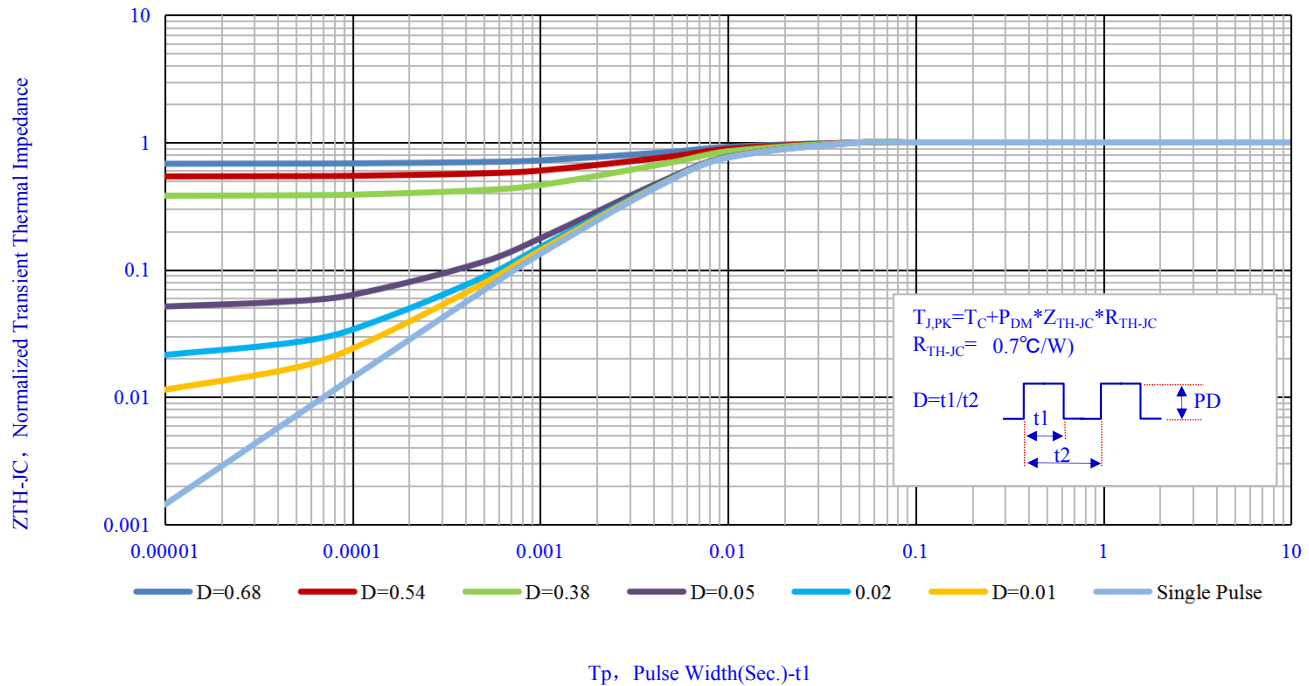


Fig.13- Normalized Maximum Transient Thermal Impedance vs.Pulse Width

Test Circuit & Waveform

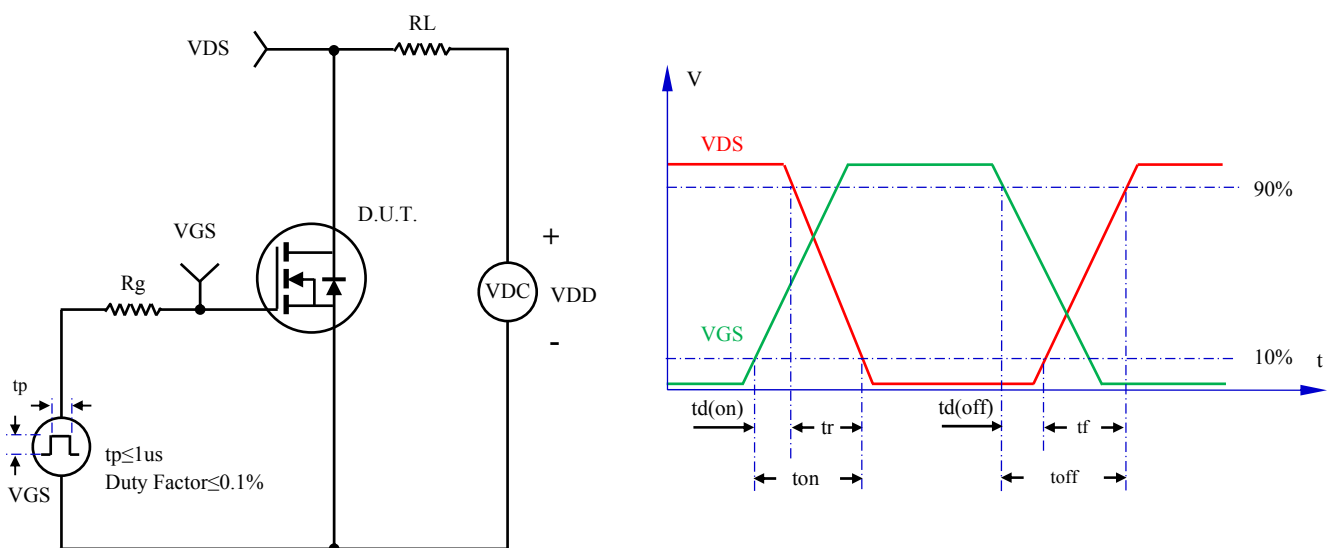


Fig.14- Resistive Switching Test Circuit & Waveform

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Test Circuit & Waveform

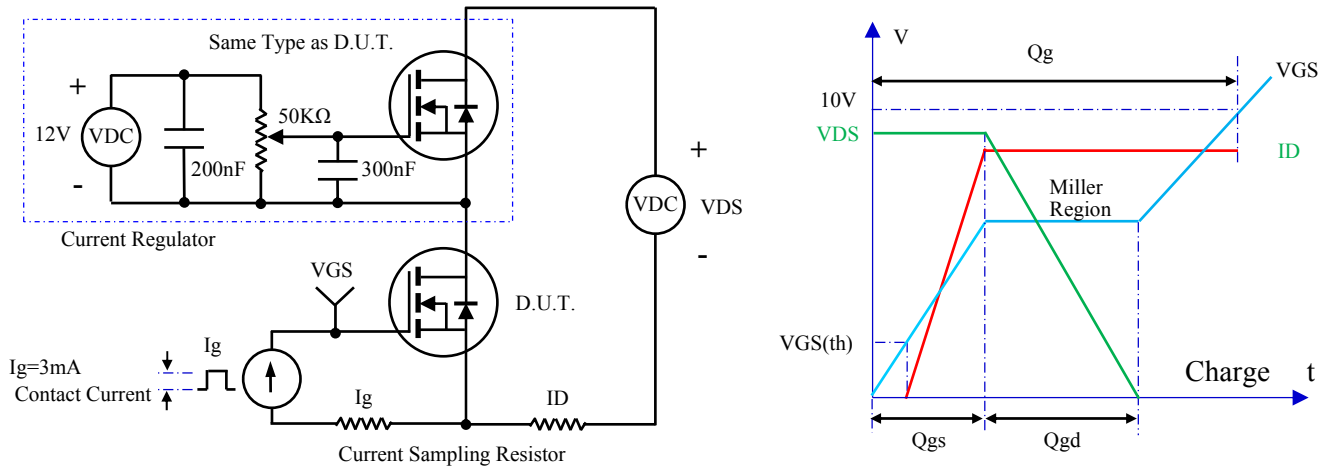


Fig.15- Gate Charge Test Circuit & Waveform

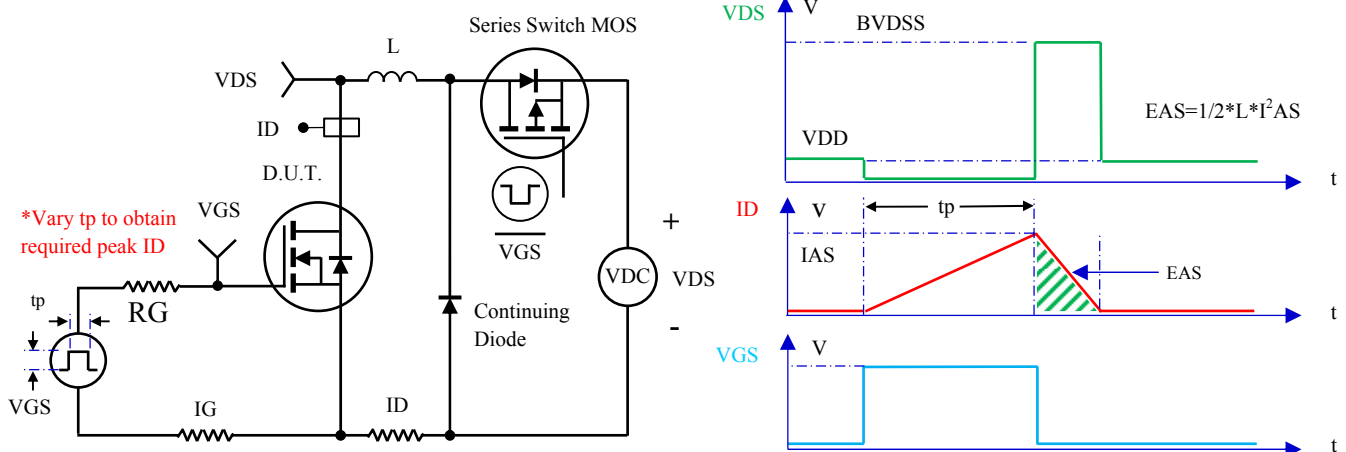


Fig.16- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

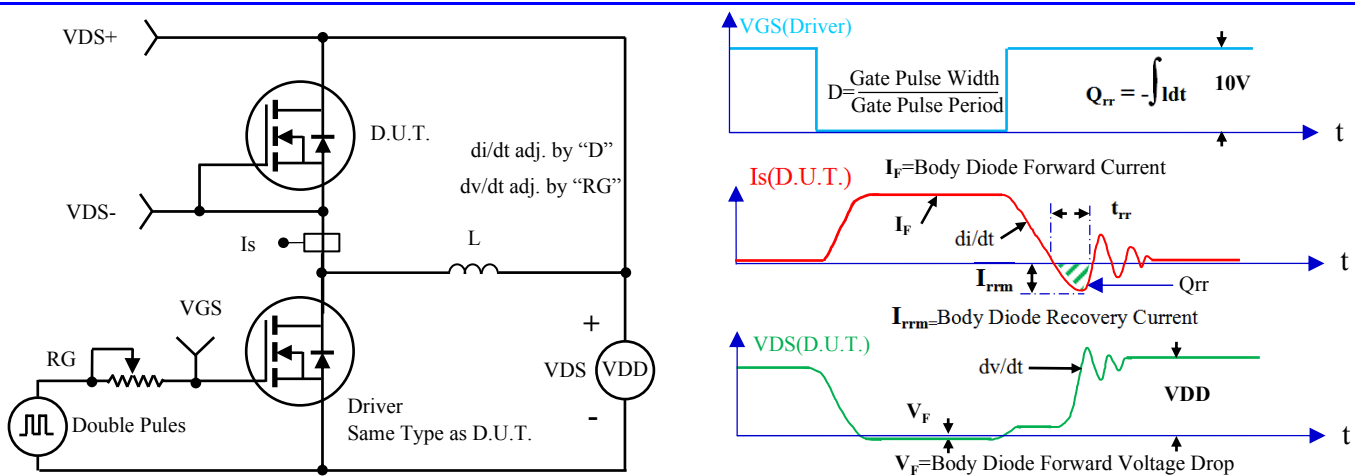


Fig.17- Diode Recovery Test Circuit & Waveform

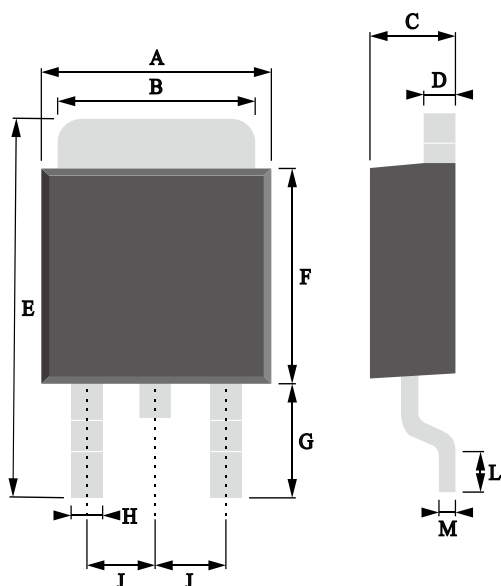
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OUTLINE DRAWINGS

TO-252

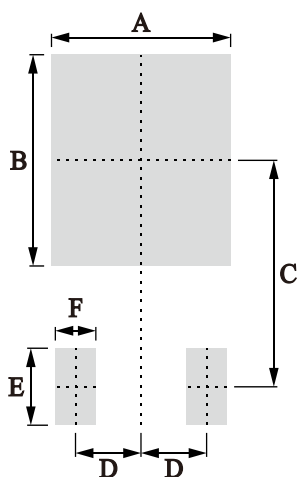


OUTLINE DIMENSIONS

Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.10	-	7.10	0.24	-	0.28
B	4.80	-	5.80	0.19	-	0.23
C	1.95	-	2.55	0.08	-	0.10
D	0.35	-	0.75	0.01	-	0.03
E	9.25	-	10.75	0.36	-	0.42
F	5.60	-	6.60	0.22	-	0.26
G	2.50	-	3.10	0.10	-	0.12
H	0.65	-	1.05	0.03	-	0.04
J	2.10	-	2.50	0.08	-	0.10
L	1.00	-	1.40	0.04	-	0.06
M	0.35	-	0.75	0.01	-	0.03

RECOMMEDNED LAYOUT DRAWINGS

TO-252



OUTLINE DIMENSIONS

Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	6.09	-	-	0.24	-
B	-	7.57	-	-	0.30	-
C	-	6.64	-	-	0.26	-
D	-	2.30	-	-	0.09	-
E	-	2.76	-	-	0.11	-
F	-	1.42	-	-	0.06	-

PACKING INFORMATION

Package Code	Package Method	Min. Pack. Size (mm)	Quantity (Pcs/Min. Pack.)	Inner Box Size L×W×H(mm)	Quantity (Pcs/Inner Box)	Outer Carton Size L×W×H(mm)	Quantity (Pcs/Carton)
TO-252	T/R	Φ330	2500	360×360×50	5000	380x380x340	30000

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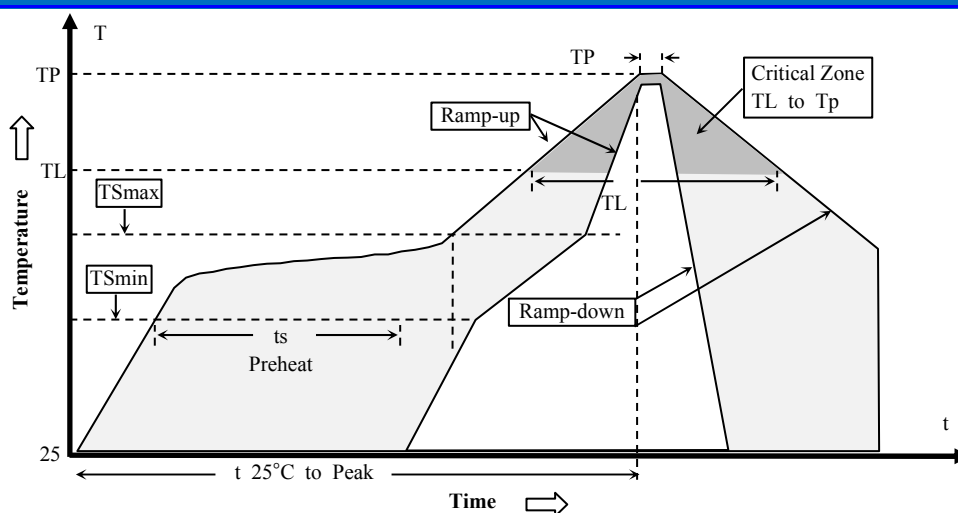
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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat -Temperature Min(T _S min) -Temperature Max(T _S max) -Time(t _s min to t _s max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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